

Substitute for form 1449B/PTO				<i>Complete if Known</i>	
				Application Number	09/838,316
				Filing Date	4/20/01
				First Named Inventor	Lu
				Group Art Unit	Unknown 213
				Examiner Name	Unassigned <i>Sark Chan</i>
Sheet	1	of	1	Attorney Docket Number	95-153

OTHER PRIOR ART — NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			
<i>~</i>		J. STOEMENOS et al, "Dislocation formations related with high oxygen dose implantation on silicon." J. App1 Phys., 69(1991), p.793.			
<i>~</i>		D. HILL et al, "The reduction of dislocations in oxygen implanted silicon on insulator layers by sequential implantation and annealing." J. App1 Phys., 63(1998), p. 4933.			
<i>~</i>		S. NAKASHIMA et al, "Investigations on high temperatures thermal oxidataion press at top and bottom interfaces of top silicon of SIMOX wafers." J. Electrochem. Soc., p. 244, 1996.			
<i>~</i>		L. NESBIT et al, "Microstructure of silicon implanted with high dose of nitrogen and oxygen." J. Electrochem. Soc., 133(1986), p.1186.			

Examiner Signature	<i>Sark Chan</i>	Date Considered	<i>11/26/02</i>
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.